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Karen Cinq-Mars 10/6/03
(Signature & date)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of : October 6, 2003
John Bruley et al. : Group Art Unit:
Serial No. 10/605,258 : Examiner:
Filed: 09/18/2003 : International Business Machines Corporation
2070 Route 52
Hopewell Junction, NY 12533

TITLE: Site-Specific Methodology for Localization and Analyzing Junction Defects in MOSFET Devices

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to the duty of disclosure set forth in 37 C.F.R. 1.56, and further pursuant to the provisions of 37 C.F.R. 1.97 and 1.98, applicants hereby respectfully submit copies of the non-US patents and publications as listed on Form PTO-1449, attached hereto.

In citing these documents, no representation is made nor intended as to the pertinency or non-pertinency of the art, that better art than that listed is not available, or that other art is not applicable.

No fee is believed to be due for this submission. If any fees are required, however, the Commissioner is hereby authorized to charge such fees to Deposit Account No. 09-0458.

Respectfully submitted,
John Bruley et al.

By: Tiffany Townsend
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FORM 100-1449 (Modified)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO.: FIS920030145US1	SERIAL NO.:
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		APPLICANT: John Bruley et al.	
(Use several sheets if necessary) (37 CFR 1.98(b))		FILING DATE:	GROUP:

REFERENCE DESIGNATION			U.S. PATENT DOCUMENTS				
EXAMINER INITIAL		PATENT NUMBER	ISSUE DATE	PATENTEE	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						

FOREIGN PATENT DOCUMENTS

			PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUB- CLASS	TRANSLATION	
		DOCUMENT NUMBER					YES	NO
	AJ							
	AK							
	AL							

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

	AM	Two Dimensional Mapping of the Electrostatic Potential in Transistors by Electron Holography, W.D. Rau, P. Schwander, F.H. Baumann, W. Hoppner, and A. Ourmazd, The American Physical Society, Vol. 82, No. 12, March 1999, pp. 2614-2617.
	AN	Electron Holography of Semiconductor Structures: Principles and Recent Results, Michael A. Gribelyuk, Martha R. McCartney, Microelectronic Failure Analysis Desk Reference 2002 Supplement Copyright© 2002. ASM International®, pp.69-74.
	AO	Focused Ion Beam Milling for Site Specific Scanning and Transmission Electron Microscopy Specimen Preparation, L.A. Giannuzzi, J.L. Drown, S.R. Brown, R.B. Irwin, and F.A. Stevie, pp. 347-348.
	AP	FIB Lift-Out for Defect Analysis, Lucille A. Giannuzzi, Brian W. Kempshall, Shawn D. Anderson, Brenda I. Prenitzer, and Thomas M. Moore, Microelectronic Failure Analysis Desk Reference 2002 Supplement. Copyright© 2002. ASM International®, pp.29-35.
	AQ	Mapping of Electrostatic Potential in Deep Submicron CMOS Devices by Electron Holography, M.A. Gribelyuk, M.R. McCartney, Jing Li, C.S. Murthy, P. Ronsheim, B. Doris, J.S. McMurray, S. Hegde and David J. Smith, The American Physical Society, Vol. 89, No. 2, July 2002, pp.1-4.
	AR	Visualisation of Electrically Active Areas Using Electron Holography, U. Muehle, A. Lenk, M. Lehmann and H. Lichte, Proceedings from the 28 th International Symposium for Testing and Failure Analysis, 3-7 November. 2002, pp. 39-45.
EXAMINER		DATE CONSIDERED

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and